

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 248760US0RDCONT		SERIAL NO. New Continuation of 10/188,744	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yasuo OHBA			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	4,792,958	12/20/88	OHBA, et al.			
	AB	4,809,287	02/28/89	OHBA, et al.			
	AC	4,835,117	05/30/89	OHBA, et al.			
	AD	4,949,349	08/14/90	OHBA, et al.			
	AE	4,910,743	03/20/90	OHBA, et al.			
	AF	4,928,285	05/22/90	KUSHIBE, et al.			
	AG	4,893,313	01/09/90	HATAKOSHI, et al.			
	AH	5,076,800	12/31/91	MILNES, et al.			
	AI	5,036,521	07/30/91	HATAKOSHI, et al.			
	AJ	5,168,077	12/01/92	ASHIZAWA, et al.			
	AK	5,042,043	08/20/91	HATANO, et al.			
	AL	5,005,057	04/02/91	IZUMIYA, et al.			
	AM	5,079,184	01/07/92	HATANO, et al.			
	AN	5,103,271	04/07/92	IZUMIYA, et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
	AO	2000-31588	01/28/00	JAPAN	YES	NO	
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW	Y. OHBA, et al., Japanese Journal of Applied Physics, Vol. 37 Part 2, No. 8A, pp. L 905 - L 906, "FABRICATION AND CHARACTERIZATION OF AlGa/GaN DOUBLE-HETEROLASER STRUCTURES ON SAPPHIRE SUBSTRATES USING SINGLE CRYSTALLINE AlN BUFFER LAYERS," August 1, 1998.					
	AX						
	AY						
	AZ	<input type="checkbox"/> Additional References sheet(s) attached					
Examiner				Date Considered			

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

(1 AUG 22 2002)

Form PTO 1449 (Modified) 6 TRADES DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT		ATTY DOCKET NO. 225255US0RD		SERIAL NO. 10/188,744		
		APPLICANT Yasuo OHBA				
		FILING DATE July 5, 2002		GROUP 2811		
		U.S. PATENT DOCUMENTS				
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,242,764	06/05/2001	Y. OHBA, et al.		
	AB	5,990,495	11/23/99	Y. OHBA		
	AC	5,656,832	08/12/97	Y. OHBA, et al.		
	AD	5,909,040	06/01/99	Y. OHBA, et al.		
	AE	5,929,466	07/27/99	Y. OHBA, et al.		
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					
	AL					
	AM					
	AN					
FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO	
	AO	2000-31588	01/28/2000	JAPAN (with English Abstract)		X
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)						
	AW	Y. OHBA, et al., Japanese Journal of Applied Physics, Vol. 37 Part 2, No. 8A, pps. L 905-L 906, "FABRICATION AND CHARACTERIZATION OF AlGaN/GaN DOUBLE-HETEROLASER STRUCTURES ON SAPPHIRE SUBSTRATES USING SINGLE CRYSTALLINE AlN BUFFER LAYERS," August 1, 1998				
	AX					
	AY					
	AZ				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner J. M. MONDT			Date Considered 02/05/03			

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.